

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14	US-0551373-\$.DID. OR US-5936320-\$.DID. OR US-5961713-\$.DID. OR US-6162708-\$.DID. OR US-0624531-\$.DID. OR US-6284384-\$.DID. "20020142171"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 14:40
S1	2	"6162708".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/23 16:58
S2	1112	LPD or light near3 point near3 defect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 13:25
S3	949	LPD or light near3 point near3 defect and epitax\$4 near3 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 13:43
S4	192	(LPD or light near3 point near3 defect and epitax\$4 near3 wafer) and nitrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 13:26
S5	10	(LPD or light near3 point near3 defect and epitax\$4 near3 wafer) and nitrogen and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 13:28
S6	944	LPD or light near3 point near3 defect same epitax\$4 near3 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 13:46
S7	942	LPD or light near3 point near3 defect same epitax\$4 near3 wafer and defect near4 free	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 13:47
S8	942	LPD or light near3 point near3 defect same epitax\$4 near3 wafer and defect near4 free: same (epitax\$4 near3 (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 13:50

S9	44	(LPD or light near3 point near3 defect same epitax\$4 near3 wafer and defect near4 free same (epitax\$4 near3 (film or layer))) and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 13:49
S10	19	(LPD or light near3 point near3 defect) same epitax\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 14:15
S11	58	(LPD or light near3 point near3 defect) same (cop or crystal near4 particle)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 14:25
S12	39	(LPD or light near3 point near3 defect) and epitax\$4 near3 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 14:29
S13	2	"5961713".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 14:30
S14	60	(denud\$3 or dz) same epitax\$4 and (silicon near4 wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 15:28
S15	19	((denud\$3 or dz) same epitax\$4 and (silicon near4 wafer)) and defect near1 free	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 15:39
S16	266529	SUMITOMO.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 15:40
S17	301	SUMITOMO.as. and epitax\$4 near3 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 15:40
S18	27	SUMITOMO.as. and epitax\$4 near3 wafer and dop\$3 near4 nitrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/28 14:15

S19	0	wafer adj prepared adj using adj the adj Cz	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/28 14:16
S20	8	wafer same ppm same oxygen same cz	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/28 14:17
S21	2	"20020142171".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/01 15:43
S22	6	("5961713" "5935320" "6162708").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:36
S23	35	(satoshi near2 komiya or shiro near2 yoshino or masayoshi near2 danbata).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:47
S24	8	(satoshi near2 komiya or shiro near2 yoshino or masayoshi near2 danbata).in. and nitrogen and oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/23 17:48
S25	6	(satoshi near2 komiya or shiro near2 yoshino or masayoshi near2 danbata).in. and nitrogen same oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/23 17:48
S26	0	("5961713" "5935320" "6162708").pn. and grind\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:36
S27	11	epitaxial near2 silicon near2 wafer same grind\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:37
S28	86	epitaxial near2 silicon same grind\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:44

S29	2071	(silicon si) near2 wafer same grind\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:45
S30	11	(silicon si) near2 wafer near15 grind\$6 same epitax\$5 near2 (silicon or si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:45
S31	1	(satoshi near2 komiya or shiro near2 yoshino or masayoshi near2 danbata).in. and grind\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:47
S32	363	epitax\$5 near2 (silicon or si) near2 wafer.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:49
S33	11	S32 and grind\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:48
S34	97	epitax\$5 near2 (silicon or si) near2 wafer and grind\$5 near10 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:51
S35	79	(silicon or si) near10 epitax\$5 same grind\$5 near10 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/24 11:57
S36	1	"11090803"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 14:40